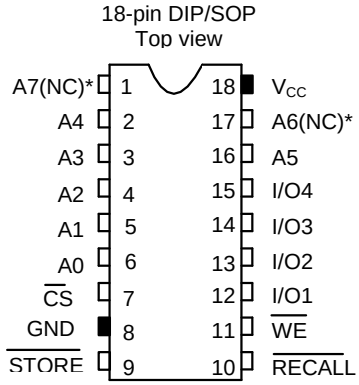
Contents

memory (E^2PROM) to backup the SRAM. The organization is word×4-bit (total 1K bits) for the S-22H12 and the S-22S12, and word×4-bit (total 256 bits) for the S-22H10 and the S-22S10.

■ Features

- 1K bits
  - S-22H12 : TTL input, compatible with the X2212 of Xicor
  - S-22S12 : Schmitt input for $\overline{\text{STORE}}$ and $\overline{\text{RECALL}}$ pins
- 256 bits
  - S-22H10 : TTL input, compatible with the X2210 of Xicor
  - S-22S10 : Schmitt input for $\overline{\text{STORE}}$ and $\overline{\text{RECALL}}$ pins
- Erroneous store protection : ≅3.5 V
- +5-V single power supply (+5 V±10%)
- Low current consumption
  - Operating : 10 mA typ.
  - Standby : 1 μA max.
- Access time: 200 ns max.
- E^2PROM store cycles : 10^5 times
- E^2PROM data retention: 10 years
- 18-pin DIP/SOP package

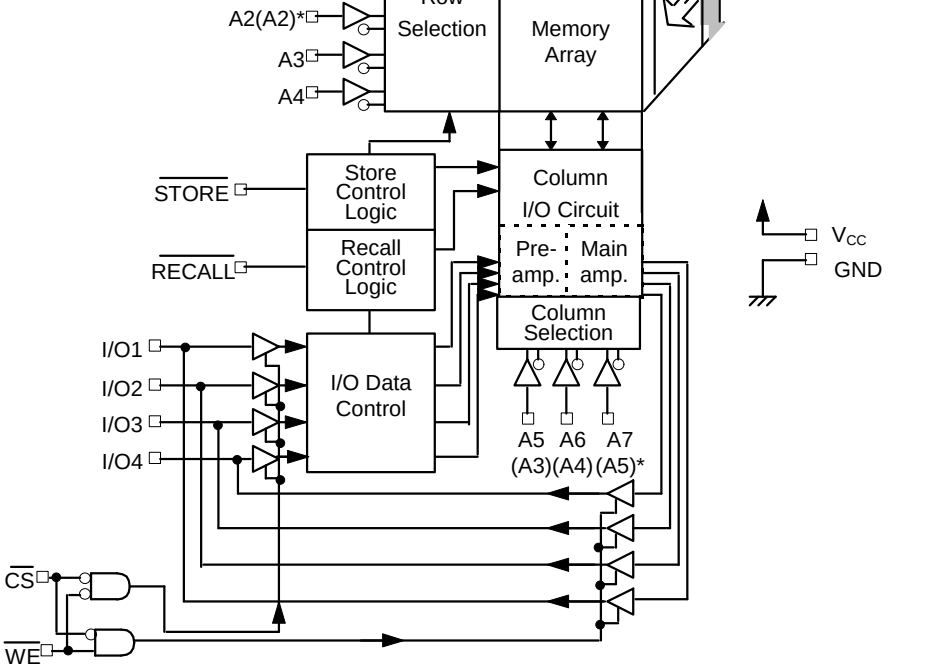
■ Pin Assignment



A0 to A7(A5)*	Address input
I/O1 to I/O4	Data input/output
$\overline{\text{WE}}$	Write enable
$\overline{\text{CS}}$	Chip select
$\overline{\text{RECALL}}$	Recall
$\overline{\text{STORE}}$	Store
GND	Ground
V_{CC}	Power supply voltage (+5 V)

*( ) is for the S-22H10 and S-22S10.

Figure 1



*( ) is for the S-22H10 and S-22S10.

Figure 2

■ Absolute Maximum Ratings

Table 1

Parameter	Symbol	Ratings	Unit
Power supply voltage	V_{CC}	-0.3 to +6.0	V
Input voltage	V_{IN}	-0.3 to V_{CC}+0.3	V
Output voltage	V_{OUT}	0.0 to V_{CC}	V
Storage temperature under bias	T_{bias}	-50 to+95	°C
Storage temperature	T_{stg}	-65 to+150	°C

■ Recommended Operating Conditions

Table 2

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Power supply voltage	V_{CC}		4.5	5.0	5.5	V
High level input voltage 1	V_{IH}	S-22H Series : All inputs S-22S Series : CS, WE, I/O and address	2.0	—	V_{CC}	V
High level input voltage 2	V_{IHS}	S-22S Series : $\overline{\text{STORE}}$ and $\overline{\text{RECALL}}$	3.4	—	V_{CC}	V
Low level input voltage 1	V_{IL}	S-22H Series : All inputs S-22S Series : CS, WE, I/O and address	0.0	—	0.8	V
Low level input voltage 2	V_{ILS}	S-22S Series : $\overline{\text{STORE}}$ and $\overline{\text{RECALL}}$	0.0	—	0.8	V
Operating temperature	T_{opr}		-40	—	+85	°C

■ DC Electrical Characteristics

Table 4

(Ta=-40°C to 85°C, V_{CC}=+5 V±10%)

Parameter	Symbol	Conditions	Min.	Typ.	Max	Unit
Operating current consumption	I_{CC}		—	10	30	mA
Standby current	I_{SB}	All inputs are V_{CC}	—	—	1	μA
Input leakage current	I_{LI}	V_{IN} =GND to V_{CC}	—	0.1	1	μA
Output leakage current	I_{LO}	V_{OUT} =GND to V_{CC}	—	0.1	1	μA
Low level output voltage	V_{OL}	CMOS : I_{OL}=100 μA	—	—	0.1	V
		TTL : I_{OL}=4.2 mA	—	—	0.4	V
High level output voltage	V_{OH}	CMOS : I_{OH}=-100 μA	V_{CC} -0.7	—	—	V
		TTL : I_{OH}=-2 mA	2.4	—	—	V
Store inhibition voltage	V_{WI}		—	3.5	4.1	V
Schmitt width	V_{WD}	S-22S Series : $\overline{\text{STORE}}$ and $\overline{\text{RECALL}}$	0.4	—	—	V

■ Data Hold Characteristics

Table 5

Parameter	Symbol	Conditions	Min.	Typ.	Max	Unit
Data hold voltage	V_{DH}	$\overline{CS}$≥V_{CC}-0.2V, $\overline{RECALL}$≥V_{CC}-0.2V	1.5	—	5.5	V
Data hold setup time	t_{CDH}		50	—	—	ns
Recovery time	t_R		300	—	—	ns

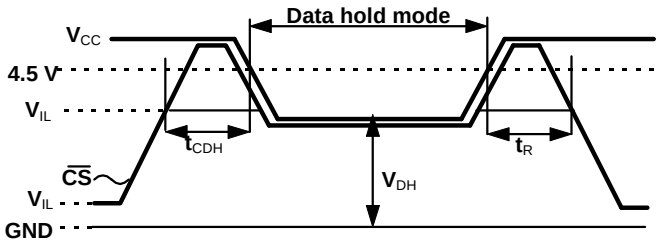


Figure 3 Data hold timing chart

	address	
	S-22S Series : $\overline{\text{STORE}}$ and $\overline{\text{RECALL}}$	0.0 to 4.0 V
Input pulse rise/fall time		10 ns
I/O reference voltage		1.5 V
Output load		1TTL+100pF

1. Read cycle

Table 7

Parameter	Symbol	Min.	Typ.	Max	Unit
Read cycle time	t_{RC}	200	—	—	ns
Address access time	t_{AA}	—	—	200	ns
$\overline{\text{CS}}$ access time	t_{CS}	—	—	200	ns
Output data hold time	t_{OH}	20	—	—	ns
Output enable time ($\overline{\text{CS}}$)	t_{CLZ}	10	—	—	ns
Output disable time ($\overline{\text{CS}}$)	t_{CHZ}	10	—	70	ns

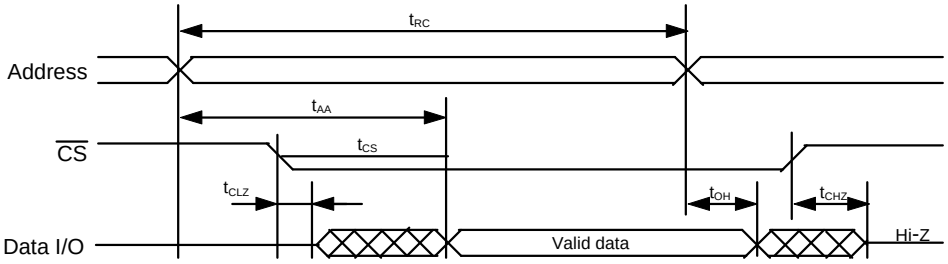


Figure 4

2. Write Cycle

Table 8

Parameter	Symbol	Min.	Typ.	Max	Unit
Write cycle time	t_{WC}	200	—	—	ns
$\overline{\text{CS}}$ pulse width	t_{CW}	120	—	—	ns
Address setup time	t_{AS}	20	—	—	ns
$\overline{\text{WE}}$ pulse width	t_{WP}	120	—	—	ns
Write reset time	t_{WR}	25	—	—	ns
Input data setup time	t_{DW}	50	—	—	ns
Input data hold time	t_{DH}	20	—	—	ns
Output disable time ($\overline{\text{WE}}$)	t_{WHZ}	10	—	70	ns
Output enable time ($\overline{\text{WE}}$)	t_{WLZ}	10	—	—	ns

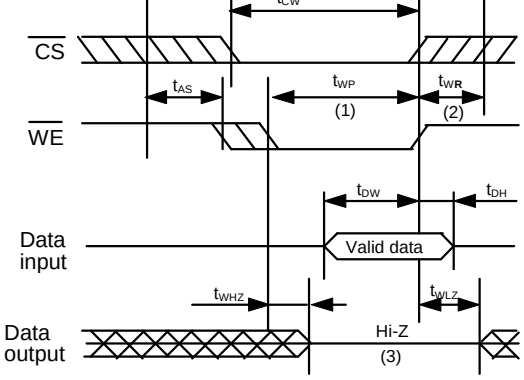


Figure 5

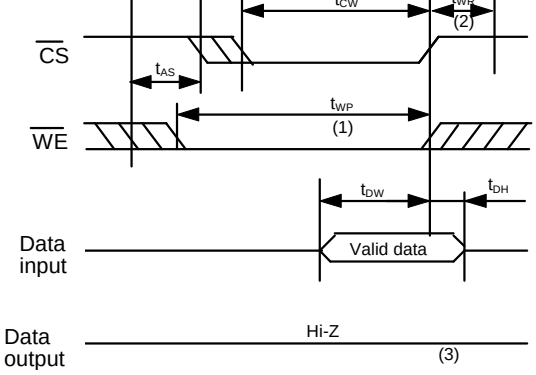


Figure 6

(1) The write cycle starts when both $\overline{CS}$ and $\overline{WE}$ are low.
(2) t_{WR} is the period of time from the rise of $\overline{CS}$ or $\overline{WE}$ whichever is the first to the end of write cycle.
(3) Output remains in high-impedance state when $\overline{CS}$ falls simultaneously with or after the fall of $\overline{WE}$.

3. Store Cycle

Table 9

Parameter	Symbol	Min.	Typ.	Max	Unit
Store time	t_{ST}	—	—	10	ms
Store pulse width	t_{STP}	200	—	—	ns
Store disable time	t_{STZ}	—	—	100	ns
Store enable time	t_{OST}	10	—	—	ns

Store operation starts at the falling of $\overline{STORE}$.

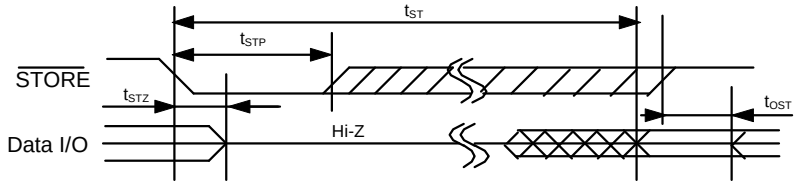


Figure 7

Recall disable time	t_{RCZ}	--	—	100	ns
Recall enable time	t_{ORC}	10	—	—	ns
Recall data access time	t_{ARC}	—	—	1100	ns

Recall operation starts at the rise of $\overline{\text{RECALL}}$. It can be repeated without limitation.

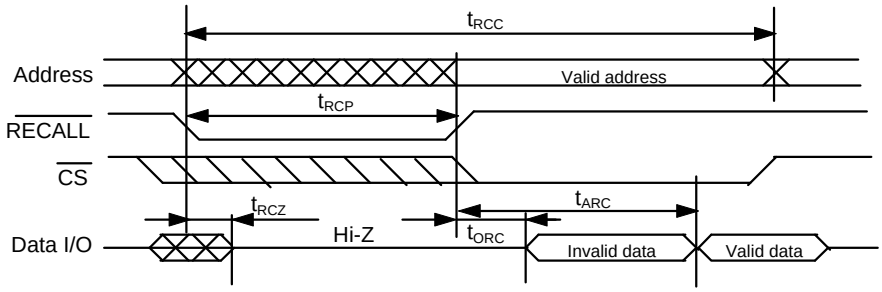


Figure 8

■ Operation Mode

Table 11

Mode	Input				Input/output
	$\overline{\text{CS}}$	$\overline{\text{WE}}$	$\overline{\text{RECALL}}$	$\overline{\text{STORE}}$	
Standby mode	H	X	H	H	Output is high impedance
Read mode	L	H	H	H	Output data
Write mode	L	L	H	H	Input data
Recall mode	X H	H X	L L	H H	Output is high impedance
Store mode	X H	H X	H H	L L	Output is high impedance

X : Don't care

Notes
- When $\overline{\text{RECALL}}$ and $\overline{\text{STORE}}$ are simultaneously input, $\overline{\text{RECALL}}$ is valid.
- When $\overline{\text{RECALL}}$ is low, $\overline{\text{STORE}}$ cannot be received.
- When power supply voltage (V_{CC}) is below store inhibition voltage V_{WI}, the store operation is inhibited.

■ Operation

1. Standby mode

When $\overline{\text{CS}}$ goes high, the S-22 Series enters into the standby mode: power consumption becomes lowest, and I/O1 to I/O4 are high impedance.

2. SRAM modes

2.1 Read mode

When $\overline{\text{CS}}$ is low and WE is high, the S-22 Series enters into the read mode: the SRAM data is output to I/O1 to I/O4.

2.2 Write mode

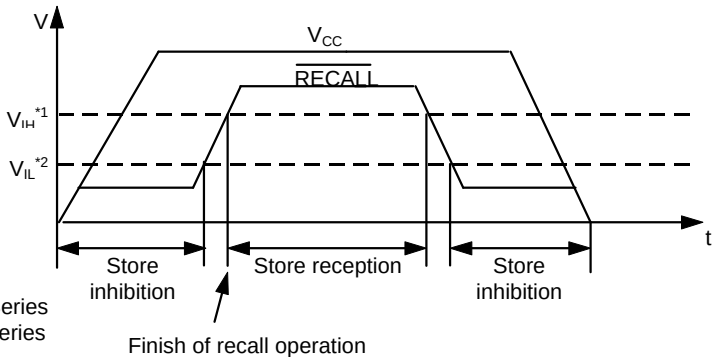
When $\overline{\text{CS}}$ and WE are low, the S-22 Series enters into the write mode: the data input in I/O1 to I/O4 is written to the SRAM.

starts, I/O1 to I/O4 go to high-impedance and other operations are inhibited until store operation is finished and $\overline{STORE}$ goes to high. During store operation, the CPU can access other instructions.

The store operation is inhibited if power supply voltage (V_{CC}) is under V_{WI} (≅3.5 V).

The following two methods prevent erroneous store, caused by noise when power turns on or off:

- $\overline{RECALL}$ goes V_{IL}(V_{ILS}) when power turns on or off (see Figure 9).
- $\overline{STORE}$ connects to V_{CC} with pull-up resistor.

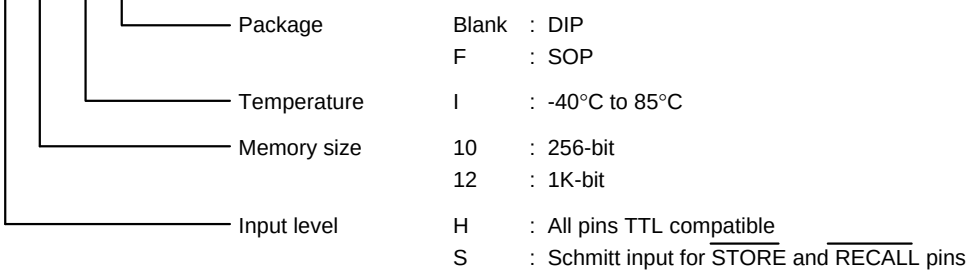


*1 V_{IHS} for the S-22S Series
*2 V_{ILS} for the S-22S Series

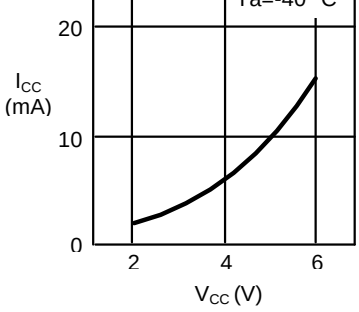
Figure 9 STORE inhibition period and reception period at power ON and OFF

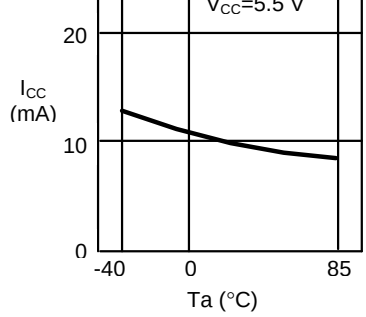
3.2 Recall mode

When $\overline{RECALL}$ goes V_{IL}(V_{ILS}), the S-22 Series enters into the recall mode: the data copied into the E^2PROM is recopied to the SRAM. The recopied data can be read or written as SRAM data. Even if the data is copied repeat the data in the E^2PROM does not change. Other operations are inhibited during its operation.

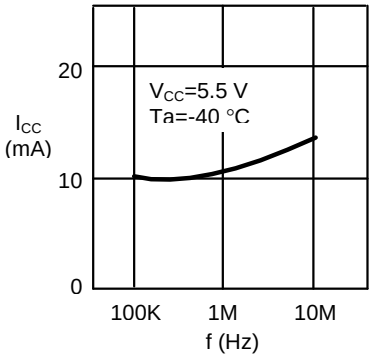


Package	Blank	: DIP
	F	: SOP
Temperature	I	: -40°C to 85°C
Memory size	10	: 256-bit
	12	: 1K-bit
Input level	H	: All pins TTL compatible
	S	: Schmitt input for $\overline{\text{STORE}}$ and $\overline{\text{RECALL}}$ pins

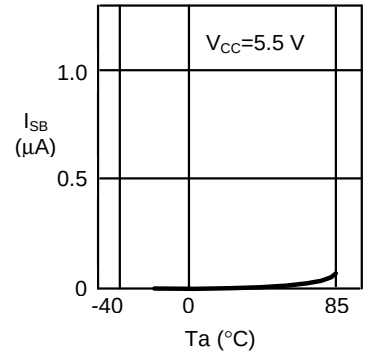




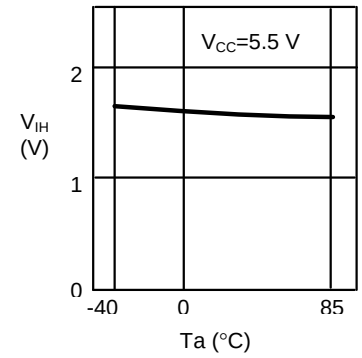
1.3 Operating current consumption I_{CC} – Reading frequency



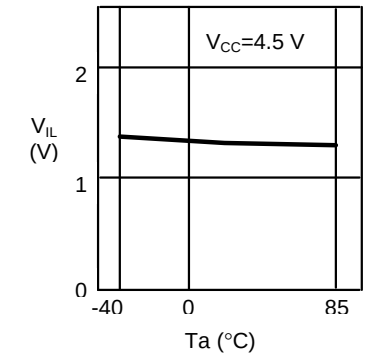
1.4 Standby current consumption I_{SB} – Ambient temperature Ta



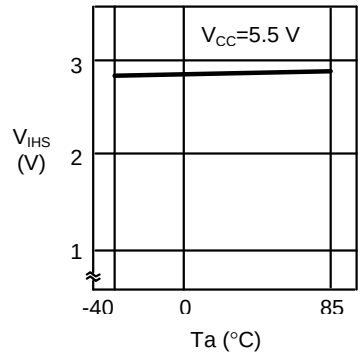
1.5 High level input voltabe V_{IH}
–Ambient temperature Ta
S-22H Series : All inputs
S-22S Series : CS, WE, I/O and address



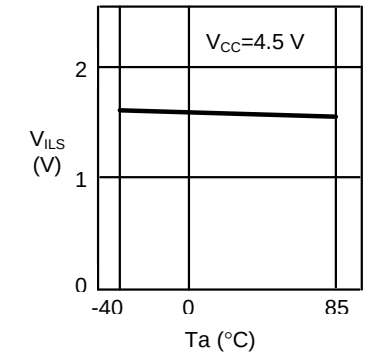
1.6 Low level input voltage V_{IL}
–Ambient temperature Ta
S-22H Series : All inputs
S-22S Series : CS, WE, I/O and address

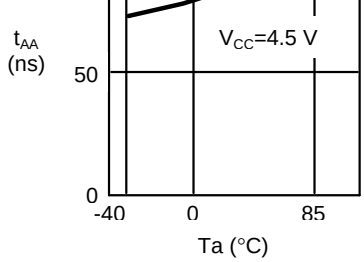


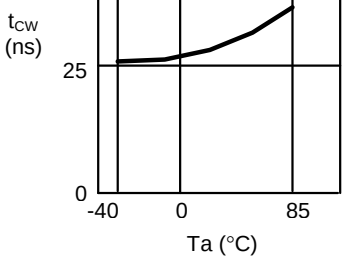
1.7 High level input voltabe V_{IHS}
–Ambient temperature Ta
S-22S Series : STORE and RECALL



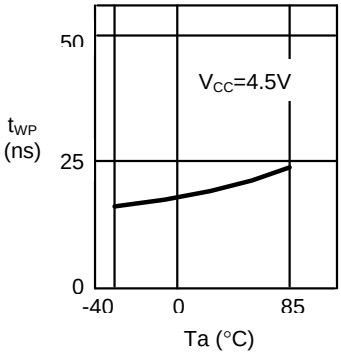
1.8 Low level input voltage V_{ILS}
–Ambient temperature Ta
S-22S Series : STORE and RECALL



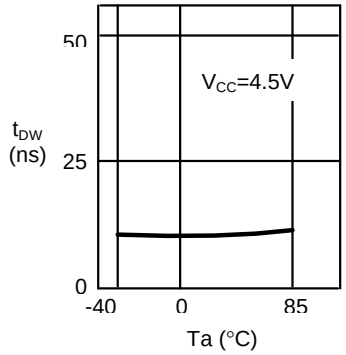




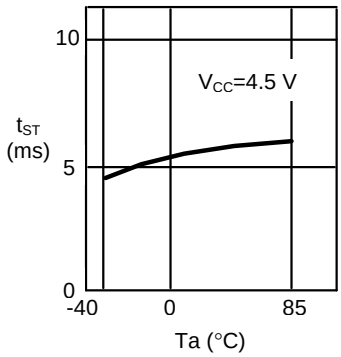
2.3 $\overline{WE}$ pulse width t_{WP}
– Ambient temperature Ta



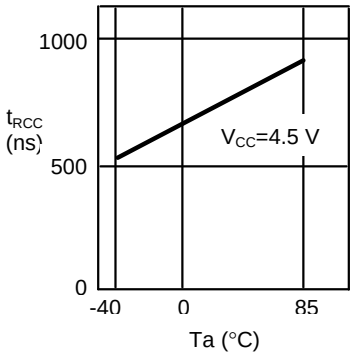
2.4 Input data setup time t_{DW}
– Ambient temperature Ta



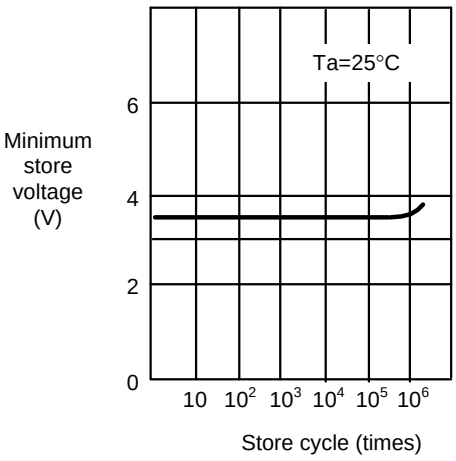
2.5 Store time t_{ST}
–Ambient temperature Ta



2.6 Recall cycle time t_{RCC}
–Ambient temperature Ta



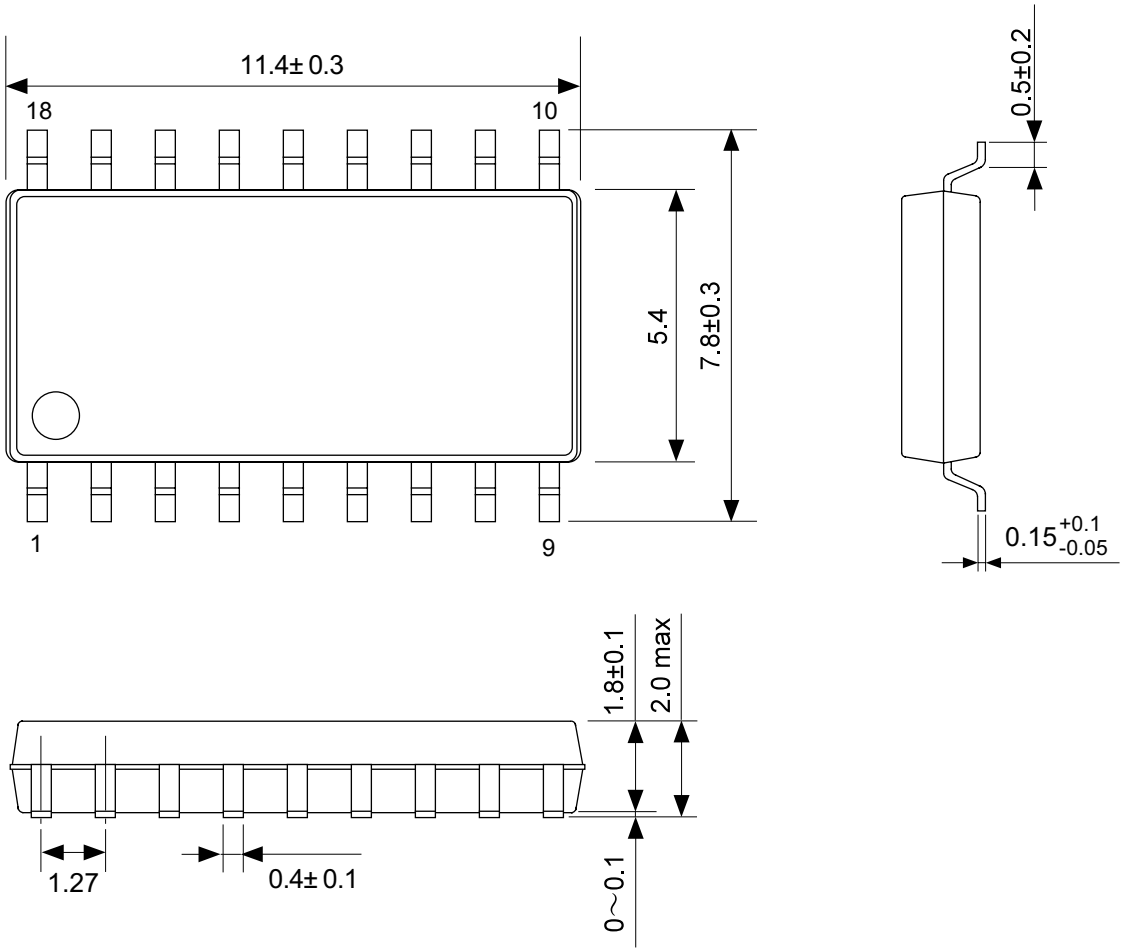
3. Rewriting Characteristics



■ 18-pin SOP

●Dimensions

Unit:mm



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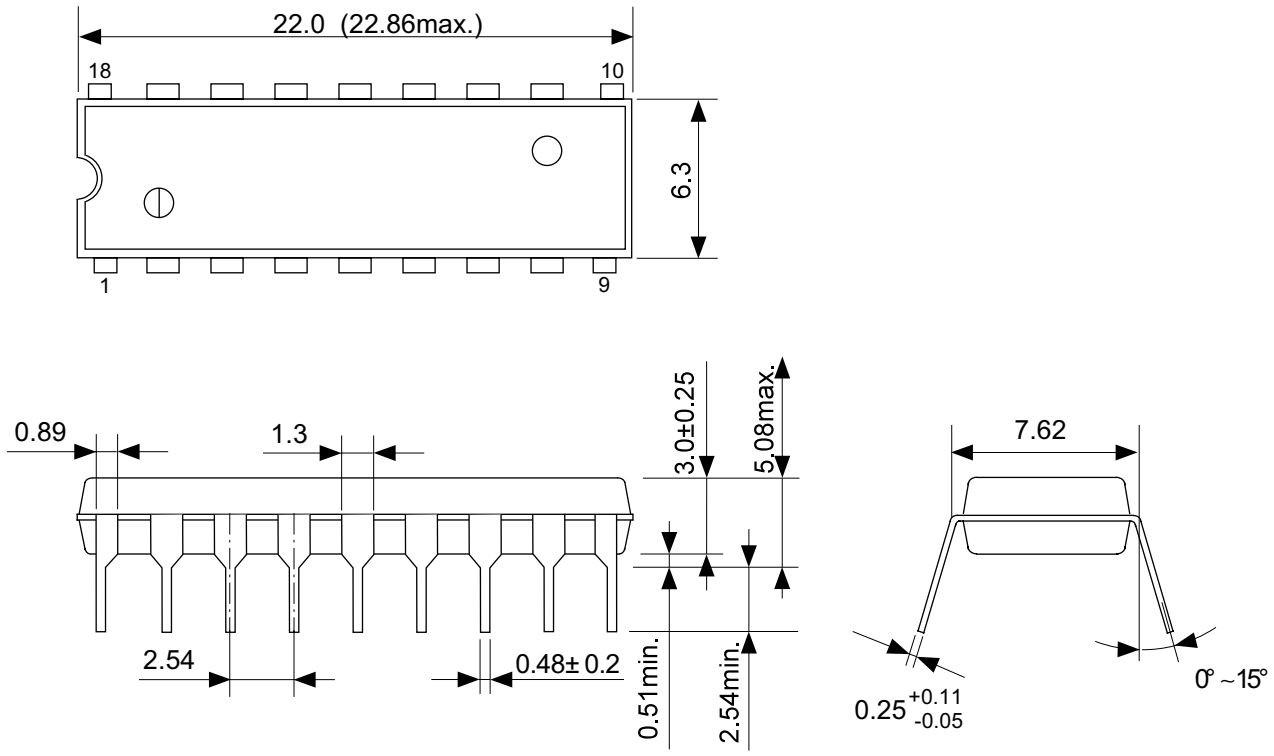
■ 18-pin DIP

DP018-A 990531

●Dimensions

Unit:mm



No. : DP018-A-P-SD-1.0

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